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博士論文題目：

三五族磊晶材料整合於矽基板上做為高速電子元件跟光電元件應用的研究

Journal

[1]. Tsung-Hsi Yang, Guangli Luo, Edward Yi Chang, **Y.C. Hsieh** and Chun-Yen Chang, "Interface-blocking Mechanism for Reduction of Threading Dislocations in SiGe and Ge Epitaxial Layers on Si(100) Substrate**, J. Vac. Sci.&Techn. B.,** Vol. 22, No. 5, pp. L17-19, Oct., 2004.

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